勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787

Http://www.100y.com.tw

1

## 200 mA, PFM Step-Up Micropower Switching Regulator

The NCP1402 series are monolithic micropower step—up DC to DC converter that are specially designed for powering portable equipment from one or two cell battery packs. These devices are designed to startup with a cell voltage of 0.8 V and operate down to less than 0.3 V. With only three external components, this series allow a simple means to implement highly efficient converters that are capable of up to 200 mA of output current at  $V_{in} = 2.0 \text{ V}$ ,  $V_{OUT} = 3.0 \text{ V}$ .

Each device consists of an on-chip PFM (Pulse Frequency Modulation) oscillator, PFM controller, PFM comparator, soft-start, voltage reference, feedback resistors, driver, and power MOSFET switch with current limit protection. Additionally, a chip enable feature is provided to power down the converter for extended battery life.

The NCP1402 device series are available in the Thin SOT-23-5 package with five standard regulated output voltages. Additional voltages that range from 1.8 V to 5.0 V in 100 mV steps can be manufactured.

#### **Features**

- Extremely Low Startup Voltage of 0.8 V
- Operation Down to Less than 0.3 V
- High Efficiency 85% ( $V_{in} = 2.0 \text{ V}, V_{OUT} = 3.0 \text{ V}, 70 \text{ mA}$ )
- Low Operating Current of 30  $\mu$ A ( $V_{OUT} = 1.9 \text{ V}$ )
- Output Voltage Accuracy ± 2.5%
- Low Converter Ripple with Typical 30 mV
- Only Three External Components Are Required
- Chip Enable Power Down Capability for Extended Battery Life
- Micro Miniature Thin SOT-23-5 Packages
- Pb-Free Packages are Available

#### **Typical Applications**

- Cellular Telephones
- Pagers
- Personal Digital Assistants (PDA)
- Electronic Games
- Portable Audio (MP3)
- Camcorders
- Digital Cameras
- Handheld Instruments

# 0N

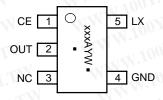
#### ON Semiconductor®

#### http://onsemi.com



SOT23-5 (TSOP-5, SC59-5) SN SUFFIX CASE 483

## PIN CONNECTIONS AND MARKING DIAGRAM



(Top View)

xxx = Marking

A = Assembly Location

Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the ordering information section on page 3 of this data sheet.

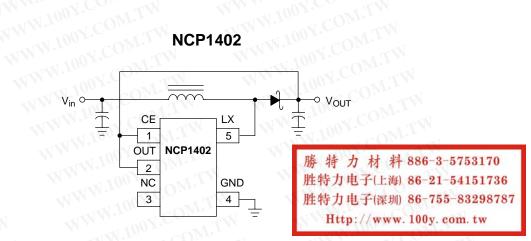


Figure 1. Typical Step-Up Converter Application

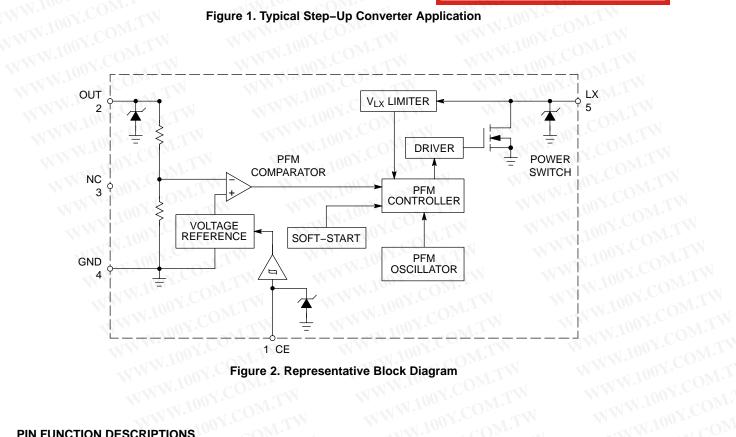


Figure 2. Representative Block Diagram

Pin #	Symbol	Pin Description
1	CE	Chip Enable pin (1) The chip is enabled if a voltage which is equal to or greater than 0.9 V is applied (2) The chip is disabled if a voltage which is less than 0.3 V is applied (3) The chip will be enabled if it is left floating
2	OUT	Output voltage monitor pin, also the power supply pin of the device
3	NC	No internal connection to this pin
4	GND	Ground pin
5	LX	External inductor connection pin to power switch drain

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#### ORDERING INFORMATION

Device	Output Voltage	Device Marking	Package	Shipping <sup>†</sup>
NCP1402SN19T1	1.9 V	DAU	SOT23-5	WT
NCP1402SN19T1G	1.9 V	DAU	SOT23-5 (Pb-Free)	OMITW
NCP1402SN27T1	2.7 V	DAE	SOT23-5	ON.TW
NCP1402SN27T1G	2.7 V	DAE	SOT23-5 (Pb-Free)	COMITW
NCP1402SN30T1	3.0 V	DAF	SOT23-5	COMIT
NCP1402SN30T1G	3.0 V	DAF	SOT23-5 (Pb-Free)	MY.COM.TW
NCP1402SN33T1	3.3 V	DAG	SOT23-5	3000 Units Per Reel
NCP1402SN33T1G	3.3 V	DAG	SOT23-5 (Pb-Free)	1.00Y.COM.TW
NCP1402SN40T1	4.0 V	DCR	SOT23-5	1100Y.COM.TW
NCP1402SN40T1G	4.0 V	DCR	SOT23-5 (Pb-Free)	W.100Y.COM.TW
NCP1402SN50T1	5.0 V	DAH	SOT23-5	MM.1001. COM.1
NCP1402SN50T1G	5.0 V	DAH	SOT23-5 (Pb-Free)	VVW.100X.COM.T

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NOTE: The ordering information lists five standard output voltage device options. Additional device with output voltage ranging from 1.8 V to 5.0 V in 100 mV increments can be manufactured. Contact your ON Semiconductor representative for availability.

#### **ABSOLUTE MAXIMUM RATINGS**

WWW.C Rating WWW.100%	Symbol	Value	Unit
Power Supply Voltage (Pin 2)	V <sub>OUT</sub>	6.0	V.
Input/Output Pins LX (Pin 5) LX Peak Sink Current	V <sub>LX</sub>	-0.3 to 6.0 400	V mA
CE (Pin 1) Input Voltage Range Input Current Range	V <sub>CE</sub>	-0.3 to 6.0 -150 to 150	V mA
Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	250	°C/W
Operating Ambient Temperature Range (Note 2)	T <sub>A</sub>	-40 to +85	°C
Operating Junction Temperature Range	W. TJCON	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

NOTES:

- This device series contains ESD protection and exceeds the following tests: Human Body Model (HBM) ±2.0 kV per JEDEC standard: JESD22–A114. Machine Model (MM) ±200 V per JEDEC standard: JESD22–A115.
- 2. The maximum package power dissipation limit must not be exceeded.

PD = 
$$\frac{T_{J(max)} - T_{A}}{R_{\theta}JA}$$

- 3. Latchup Current Maximum Rating: ±150 mA per JEDEC standard: JESD78.
- 4. Moisture Sensitivity Level: MSL 1 per IPC/JEDEC standard: J-STD-020A.

Characteristic   Symbol   Min   Typ   Max   Min   Typ   Max   Min   Typ   Max   Min   Min   Typ   Max   Min   M	SCILLATOR   Switch On Time (current limit not asserted)	ELECTRICAL CHARACTERISTICS (For all values T <sub>A</sub> = 25°C, unless otherwise noted.)			Http://www.100y.co		
Switch On Time (current limit not asserted)   t_of   d_off   1.0   1.45   1.76	Switch On Time (current limit not asserted)  \$\text{tof}\$ toff	Characteristic	Symbol	Min	Тур	Max	
Switch Minimum Off Time         Interest of the process of the	Switch Minimum Off Time	OSCILLATOR	WWW.	"VY'CO"	WT		
Maximum Duty Cycle	Maximum Duty Cycle    DMAX	Switch On Time (current limit not asserted)	t <sub>on</sub>	3.6	5.5	7.6	
Minimum Startup Voltage (I <sub>O</sub> = 0 mA)	Minimum Startup Voltage (I <sub>O</sub> = 0 mA)   V <sub>start</sub>   − 0.8   0.98	Switch Minimum Off Time	t <sub>off</sub>	1.0	1.45	1.9	
Minimum Startup Voltage (I <sub>O</sub> = 0 mA)	Minimum Startup Voltage (I <sub>O</sub> = 0 mA)	Maximum Duty Cycle	D <sub>MAX</sub>	70	78	85	
Minimum Startup Voltage Temperature Coefficient (T <sub>A</sub> = −40°C to 85°C)	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Minimum Startup Voltage (I <sub>O</sub> = 0 mA)		· Va	0.8	0.95	
Minimum Operation Hold Voltage (I <sub>O</sub> = 0 mA)	Minimum Operation Hold Voltage (I <sub>O</sub> = 0 mA)			1 - ×	-1.6	-	
Soft-Start Time (Vout > 0.8 V)	Soft-Start Time (V <sub>OUT</sub> > 0.8 V)			0.3			
Internal Switching N-Channel FET Drain Voltage	Internal Switching N-Channel FET Drain Voltage		4/1/		2.0	V. I.	
Internal Switching N-Channel FET Drain Voltage	Internal Switching N-Channel FET Drain Voltage		133	40.5	7.00	- ( 1	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I		V	TNV	~1 C	T 60	
Device Suffix:   19T1	Device Suffix:         1110         145         -         1100         145         -         130         180         -         -         130         180         -         -         130         180         -         -         130         190         -         -         130         200         -         -         130         210         -         -         50T1         130         210         -         -         0.5         50T1         130         210         -         -         0.5         10         -         -         0.5         10         -         -         0.5         10         -         -         0.5         10         -         -         0.5         1.0         -         -         0.5         1.0         -         -         0.5         1.0         -         -         0.5         1.0         -         -         0.5         1.0         -         -         -         0.5         1.0         -         -         -         -         0.5         0.0         5.0         1.0         -         -         0.3         2.0         2.0         2.0         2.0         2.0         2.0         2.0         2.0			- 1 W.	UO E.	0.0	
19T1	19T1		'LX	W VY	1007.		
33T1	330T1   130   190	19T1	W			COP	
33T1   40T1   130   200   1-	3311		- 1		4		
## A0T1	40T1		TW		- 1111	_	
50T1	50T1				7 '	1.C	
Voltage Limit         VLXLIM         0.45         0.65         0.9           Off-State Leakage Current (V <sub>LX</sub> = 6.0 V, T <sub>A</sub> = −40°C to 85°C)         I <sub>LKG</sub> −         0.5         1.0           CE (PIN 1)           CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)           High State, Device Enabled         V <sub>CE(high)</sub> V <sub>CE(low)</sub> 0.9         −         −         0.3           CE Input Current (Note 6)         High State, Device Enabled (V <sub>OUT</sub> = 6.0 V)         CE(high) (CE(high) (CE(high))         −0.5         0         0.5 <td>  Voltage Limit</td> <td></td> <td>W.r.</td> <td></td> <td>&lt; 1 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \</td> <td> (</td>	Voltage Limit		W.r.		< 1 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	(	
Off-State Leakage Current (V <sub>LX</sub> = 6.0 V, T <sub>A</sub> = −40°C to 85°C)         I <sub>LKG</sub> −         0.5         1.0           CE (PIN 1)         CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)         V <sub>CE(high)</sub> U <sub>OW</sub> = V <sub>CE(low)</sub> 0.9         −         −         −         0.3         −         −         −         0.3         −         −         −         0.3         −         −         −         0.3         −         −         −         0.3         −         −         0.3         −         −         0.3         −         −         0.3         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.0         0.5         0.5         0.5         0.5         0.0         0.5         0.5         0.5         0.5         0.5         0.5         0.5         0.5         0.5         0.5         0.5         0.5	Off–State Leakage Current (V <sub>LX</sub> = 6.0 V, T <sub>A</sub> = −40°C to 85°C)  E (PIN 1)  CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96) High State, Device Enabled  V <sub>CE(low)</sub> U <sub>OE(low)</sub> V <sub>CE(low)</sub> U <sub>OE(low)</sub> U <sub>OE(lo</sub>		VLXLIM	0.45		0.9	
CE (PIN 1)   CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)   High State, Device Enabled   V <sub>CE(high)</sub>   0.9	E (PIN 1)   CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)   High State, Device Enabled   V <sub>CE(high)</sub>   0.9			_ \( \)	0.5	1.0	
CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)   High State, Device Enabled   V <sub>CE(high)</sub> State, Device Disabled   V <sub>CE(high)</sub>	CE Input Voltage (V <sub>OUT</sub> = V <sub>SET</sub> x 0.96)     High State, Device Disabled   V <sub>CE(high)</sub>   0.9   -   -   0.3     CE Input Current (Note 6)     High State, Device Enabled (V <sub>OUT</sub> = V <sub>CE</sub> = 6.0 V)     Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)     Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)     Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)     Device Suffix:		OMLENG		NWW	- 004	
High State, Device Enabled	High State, Device Enabled		-OM-	r	TANK	1.100	
Low State, Device Disabled         VCE(tow)         −         −         0.3           CE Input Current (Note 6) High State, Device Enabled (VOUT = VCE = 6.0 V) Low State, Device Disabled (VOUT = 6.0 V, VCE = 0 V)         ICE(high) ICE(low)         −0.5 −0.5         0         0.5 0.15         0.5           TOTAL DEVICE           Output Voltage Device Suffix: 1971 2771         VOUT         1.853 2.925 3.0 3.07 3.218 3.218 3.3 3.218 3.300 3.301 4.071 4.875         1.94 2.925 3.0 3.07 3.218 3.300 3.218 3.300 4.0 <b< td=""><td>Low State, Device Disabled         VCE(low)         -         -         0.3           CE Input Current (Note 6)         High State, Device Enabled (V<sub>OUT</sub> = V<sub>CE</sub> = 6.0 V)         I<sub>CE(high)</sub>         -0.5         0.15         0.5           Low State, Device Disabled (V<sub>OUT</sub> = 6.0 V, V<sub>CE</sub> = 0 V)         I<sub>CE(low)</sub>         -0.5         0.15         0.5           OTAL DEVICE           Output Voltage           Device Suffix:         1971         2.632         2.7         2.76           30T1         2.925         3.0         3.07           33T1         3.218         3.3         3.81           40T1         3.900         4.0         4.10           50T1         4.875         5.0         5.12           Output Voltage Temperature Coefficient (T<sub>A</sub> = -40°C to +85°C)         ΔV<sub>OUT</sub>         -         150         -           Device Suffix:         -         150         -         150         -           33T1         -         150         -         150         -           40T1         -         150         -         150         -           33T1         -         150         -         150         -           40T1<td></td><td>VCE(bigh)</td><td>0.9</td><td>11 7</td><td>100</td></td></b<>	Low State, Device Disabled         VCE(low)         -         -         0.3           CE Input Current (Note 6)         High State, Device Enabled (V <sub>OUT</sub> = V <sub>CE</sub> = 6.0 V)         I <sub>CE(high)</sub> -0.5         0.15         0.5           Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)         I <sub>CE(low)</sub> -0.5         0.15         0.5           OTAL DEVICE           Output Voltage           Device Suffix:         1971         2.632         2.7         2.76           30T1         2.925         3.0         3.07           33T1         3.218         3.3         3.81           40T1         3.900         4.0         4.10           50T1         4.875         5.0         5.12           Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)         ΔV <sub>OUT</sub> -         150         -           Device Suffix:         -         150         -         150         -           33T1         -         150         -         150         -           40T1         -         150         -         150         -           33T1         -         150         -         150         -           40T1 <td></td> <td>VCE(bigh)</td> <td>0.9</td> <td>11 7</td> <td>100</td>		VCE(bigh)	0.9	11 7	100	
CE Input Current (Note 6)   High State, Device Enabled (Vout = Voe = 6.0 V)	CE Input Current (Note 6)  High State, Device Enabled (Vout = VCE = 6.0 V)  Low State, Device Disabled (Vout = 6.0 V, VCE = 0 V)  OTAL DEVICE  Dutput Voltage  Device Suffix:  19T1  27T1  30T1  2.632  2.7  2.766  3.0  3.311  40T1  Device Suffix:  19T1  - 150 - 27T1  30T1  30T1  30T1  30T1  30T1  30T1  30T1  30T1  40T1  Device Suffix:  19T1  - 150			<b>√</b> -	14 W	0.3	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	High State, Device Enabled (V <sub>OUT</sub> = V <sub>CE</sub> = 6.0 V) Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)  OTAL DEVICE  Dutput Voltage Device Suffix:  19T1 27T1 30T1 2.632 2.77 33T1 2.632 2.77 33T1 3.218 3.218 3.33 3.38 40T1 50T1  Device Suffix:  19T1 27T1 30T1 3.71 3.71 3.71 3.71 3.71 3.71 3.71 3.7	CE Input Current (Note 6)	4 COM.	- 51	×1×1	M.J	
Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)         I <sub>CE(low)</sub> -0.5         0.15         0.5           TOTAL DEVICE           Output Voltage Device Suffix:         1911         1.853         1.9         1.94t           27T1         2.632         2.7         2.76t           30T1         3.263         2.7         2.76t           30T1         3.218         3.3         3.38t           40T1         3.900         4.0         4.10t           50T1         4.875         5.0         5.12t           Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)         ΔV <sub>OUT</sub> -         150         -           Device Suffix:         -         150         -         -         150         -           33T1         -         150         -         -         150         -           33T1         -         150         -         -         150         -           40T1         -         150         -         -         150         -           33T1         -         150         -         -         150         -           0perating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> × 0.96)         I <sub>DD1</sub> <t< td=""><td>Low State, Device Disabled (V<sub>OUT</sub> = 6.0 V, V<sub>CE</sub> = 0 V)         I<sub>CE</sub>(low)         −0.5         0.15         0.5           OTAL DEVICE           Output Voltage         V<sub>OUT</sub>         1.853         1.9         1.94           27T1         2.632         2.7         2.76           30T1         3.218         3.3         3.38           40T1         3.900         4.0         4.10           50T1         4.875         5.0         5.12           Output Voltage Temperature Coefficient (T<sub>A</sub> = −40°C to +85°C)         ΔV<sub>OUT</sub>         —         150         −           19T1         -         150         −         150         −           27T1         -         150         −         150         −           33T1         -         150         −         150         −           33T1         -         150         −         150         −           40T1         -         150         −         150         −           50T1         -         150         −         150         −           0Perating Current 2 (V<sub>OUT</sub> = V<sub>CE</sub> = V<sub>SET</sub> x 0.9 K, V<sub>CE</sub> = 0 V, T<sub>A</sub> = −40°C to +85°C, Note 6)         I<sub>OE</sub>F         −         0.6         1.0&lt;</td><td></td><td>I<sub>CE(hiah)</sub></td><td>-0.5</td><td>0</td><td>0.5</td></t<>	Low State, Device Disabled (V <sub>OUT</sub> = 6.0 V, V <sub>CE</sub> = 0 V)         I <sub>CE</sub> (low)         −0.5         0.15         0.5           OTAL DEVICE           Output Voltage         V <sub>OUT</sub> 1.853         1.9         1.94           27T1         2.632         2.7         2.76           30T1         3.218         3.3         3.38           40T1         3.900         4.0         4.10           50T1         4.875         5.0         5.12           Output Voltage Temperature Coefficient (T <sub>A</sub> = −40°C to +85°C)         ΔV <sub>OUT</sub> —         150         −           19T1         -         150         −         150         −           27T1         -         150         −         150         −           33T1         -         150         −         150         −           33T1         -         150         −         150         −           40T1         -         150         −         150         −           50T1         -         150         −         150         −           0Perating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.9 K, V <sub>CE</sub> = 0 V, T <sub>A</sub> = −40°C to +85°C, Note 6)         I <sub>OE</sub> F         −         0.6         1.0<		I <sub>CE(hiah)</sub>	-0.5	0	0.5	
Output Voltage Device Suffix: 19T1 27T1 30T1 30T1 2.632 2.77 2.632 2.77 2.632 2.77 2.763 3.07 3.218 3.30 3.900 4.0 4.875 5.0 5.12           Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C) Device Suffix: 19T1 27T1 30T1 30T1 30T1 30T1 50T1         ΔV <sub>OUT</sub> 4.75 5.0 5.12           Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C) Device Suffix: 19T1 27T1 30T1 30T1 50T1         Device Suffix: 150 - 150 - 150 - 150           Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)         I <sub>DD2</sub> -         13         15           Off-State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)         I <sub>OFF</sub> -         0.6         1.0           Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96) Device Suffix: 19T1 27T1 30T1 30T1 30T1 30T1 30T1 30T1 30T1 30	Dutput Voltage         Vout         In the property of the property			-0.5	0.15	0.5	
Device Suffix:       19T1       1.853       1.9       1.944         27T1       2.632       2.7       2.766         30T1       2.925       3.0       3.07         33T1       3.218       3.3       3.38         40T1       3.900       4.0       4.10         50T1       4.875       5.0       5.12         Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)       ΔV <sub>OUT</sub> ΔV <sub>OUT</sub> -         Device Suffix:       -       150       -         19T1       -       150       -         27T1       -       150       -         33T1       -       150       -         40T1       -       150       -         50T1       -       150       -         Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)       I <sub>DD2</sub> -       13       15         Off-State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)       I <sub>OFF</sub> -       0.6       1.0         Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)       I <sub>DD1</sub> -       -       30       50         27T1       -       -       42       60         33T1<	Device Suffix:       1,853       1,9       1,944         27T1       2,632       2,7       2,76         30T1       2,925       3,0       3,07         33T1       3,218       3,3       3,38         40T1       3,900       4,0       4,10         50T1       4,875       5,0       5,12         Output Voltage Temperature Coefficient (T <sub>A</sub> = −40°C to +85°C)       ΔV <sub>OUT</sub> -         Device Suffix:       -       150       -         19T1       -       150       -         27T1       -       150       -         30T1       -       150       -         33T1       -       150       -         40T1       -       150       -         50Tf-State Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)       I <sub>DD2</sub> -       13       15         Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)       I <sub>DD1</sub> -       0.6       1.0         Device Suffix:       -       33       50       50       50       1.0       50         19T1       -       30       50       50       50       50       50       50         27T1       <	TOTAL DEVICE	COM	- N		NWW	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	19T1		Vout	1. 1.		-131	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	27T1 2.632 2.7 2.76 30T1 2.925 3.0 3.07 33T1 3.218 3.3 3.38 40T1 3.900 4.0 4.10 50T1 ΔV <sub>OUT</sub> Device Suffix:  19T1 - 150 - 27T1 - 150 - 33T1 - 150 - 33T1 - 150 - 31T1 - 150 - 30T1 - 150 - 150 - 30T1 -		100 Y.C			M.	
30T1 33T1 40T1 50T1  Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C) Device Suffix:  19T1 27T1 30T1 30T1 30T1 30T1 30T1 30T1 30T1 30	30T1 33T1 33T1 33T1 40T1 50T1  Dutput Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)  Device Suffix:  19T1 27T1 30T1 30T1 30T1 30T1 30T1 30T1 30T1 30		· CO				
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	33T1		U 100 1.				
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	40T1 50T1 3.900 4.0 4.100 5.121  Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)  Device Suffix:  19T1 - 150 - 27T1 - 150 - 30T1 - 150 - 150 - 33T1 - 150 - 15		O.V.C				
SoT1	50T1		W.100				
Device Suffix:  19T1  27T1  30T1  30T1  40T1  50T1   Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)  Operating Current 1 (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)  Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)  Device Suffix:  19T1  27T1  30T1  - 30 50  30T1  30T1  - 42 60  33T1	Device Suffix:  19T1 - 150 - 27T1 - 150 - 30T1 - 150 - 33T1 - 150 - 40T1 - 150 - 50T1 - 150 -  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)		100Y.				
Device Suffix:  19T1 - 150 - 27T1 - 150 - 30T1 - 150 - 33T1 - 150 - 40T1 - 150 - 50T1 - 150 -  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)	Device Suffix:  19T1 - 150 - 27T1 - 150 - 30T1 - 150 - 33T1 - 150 - 40T1 - 150 - 50T1 - 150 -  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)	Output Voltage Temperature Coefficient (T <sub>A</sub> = -40°C to +85°C)	$\Delta V_{OUT}$	· CO	CM	1	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	27T1	Device Suffix:	WW.Jo.	A COM			
30T1 33T1 40T1 50T1  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)  Off–State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)  Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)  Device Suffix:  19T1 27T1 30T1 30T1 30T1 33T1	30T1 33T1 40T1 50T1  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)  Off-State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)  Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)  Device Suffix:  19T1 27T1 30T1 30T1 30T1 30T1 30T1 30T1 40T1		100	-01	1.0	_	
33T1 40T1 50T1  Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)  Off–State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)  Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)  Device Suffix:  19T1 27T1 30T1 30T1 30T1 33T1	33T1 40T1 50T1  ———————————————————————————————————		WWW.	V.Gos	~ 11. 11.	_	
40T1 50T1  - 150	40T1		. M.J.	700		_	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	50T1		MM	001.		_	
Operating Current 2 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> +0.5 V, Note 5)       I <sub>DD2</sub> -       13       15         Off-State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)       I <sub>OFF</sub> -       0.6       1.0         Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)       I <sub>DD1</sub> -       30       50         Device Suffix:       -       39       60         30T1       -       42       60         33T1       -       45       60	Departing Current 2 (Vout = VcE = Vset +0.5 V, Note 5)   IDD2   - 13   15		WWW.	I.C	y	_	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Off-State Current (V <sub>OUT</sub> = 5.0 V, V <sub>CE</sub> = 0 V, T <sub>A</sub> = -40°C to +85°C, Note 6)  Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)  Device Suffix:  19T1  - 30 50  27T1  - 39 60  30T1  - 42 60  33T1  40T1		Inna	100 -		15	
Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)       I <sub>DD1</sub> Device Suffix:       -         19T1       -         27T1       -         30T1       -         33T1       -         45       60	Operating Current 1 (V <sub>OUT</sub> = V <sub>CE</sub> = V <sub>SET</sub> x 0.96)       I <sub>DD1</sub> Device Suffix:       -       30       50         19T1       -       39       60         27T1       -       42       60         30T1       -       45       60         40T1       -       55       100		- 1			-	
Device Suffix:  19T1  27T1  30 50  - 39 60  30T1  - 42 60  33T1	Device Suffix:  19T1  27T1  30 50  50  60  30T1  33T1  40T1  - 45 60  - 55 100			+	0.0	1.0	
33T1 - 42 60 - 45 60	33T1 - 45 60 40T1 - 55 100	Device Suffix:	DD1				
33T1 - 45 60	33T1 - 45 60 40T1 - 55 100	19T1	1	_	30	50	
33T1	33T1 - 45 60 40T1 - 55 100	27T1		_			
	40T1 - 55 100	3011		_	42	60	
40T1     -   55   100				_			
		40T1	ĺ	I –	55	I 100	

<sup>5.</sup>  $V_{SET}$  means setting of output voltage. 6. CE pin is integrated with an internal 10 M $\Omega$  pullup resistor.

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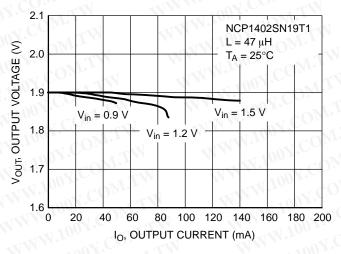


Figure 3. NCP1402SN19T1 Output Voltage vs. **Output Current** 

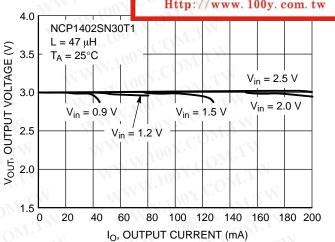


Figure 4. NCP1402SN30T1 Output Voltage vs. **Output Current** 

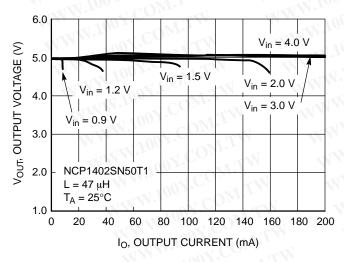


Figure 5. NCP1402SN50T1 Output Voltage vs. **Output Current** 

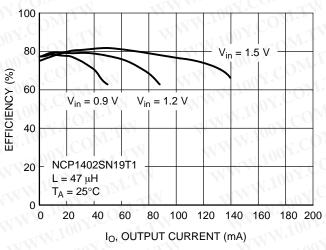


Figure 6. NCP1402SN19T1 Efficiency vs. **Output Current** 

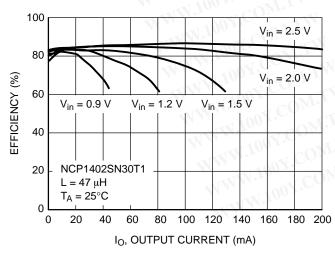


Figure 7. NCP1402SN30T1 Efficiency vs. **Output Current** 

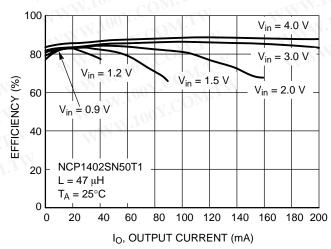


Figure 8. NCP1402SN50T1 Efficiency vs. **Output Current** 

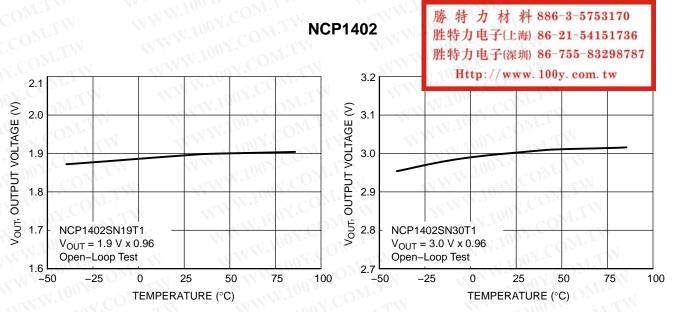


Figure 9. NCP1402SN19T1 Output Voltage vs. Temperature

Figure 10. NCP1402SN30T1 Output Voltage vs. Temperature

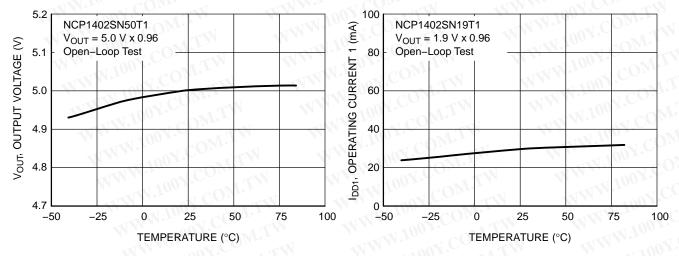


Figure 11. NCP1402SN50T1 Output Voltage vs. Temperature

Figure 12. NCP1402SN19T1 Operating Current 1 vs. Temperature

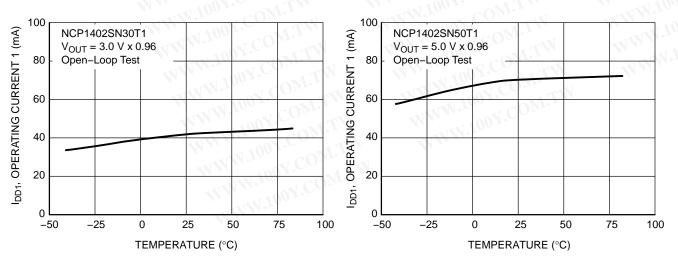


Figure 13. NCP1402SN30T1 Operating Current 1 vs. Temperature

Figure 14. NCP1402SN50T1 Operating Current 1 vs. Temperature

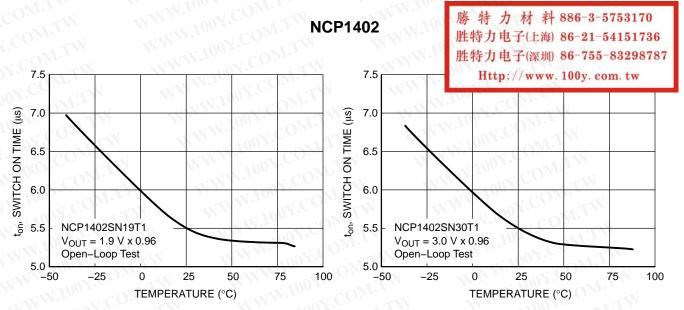


Figure 15. NCP1402SN19T1 Switch On Time vs. Temperature

Figure 16. NCP1402SN30T1 Switch On Time vs. Temperature

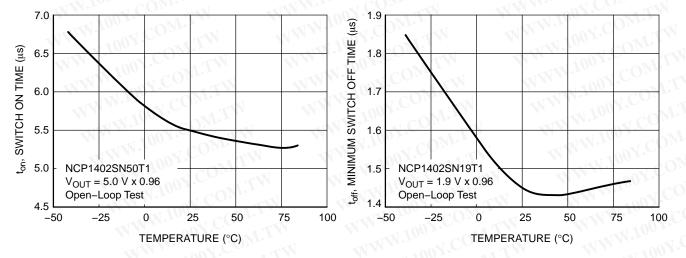


Figure 17. NCP1402SN50T1 Switch On Time vs. Temperature

Figure 18. NCP1402SN19T1 Minimum Switch Off Time vs. Temperature

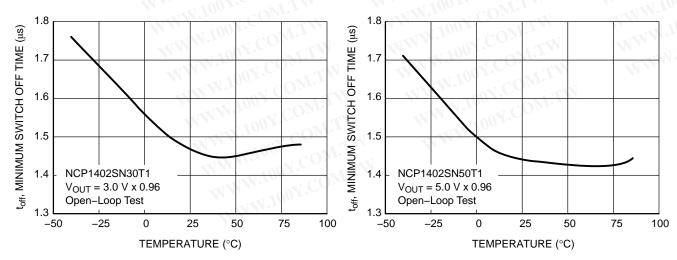


Figure 19. NCP1402SN30T1 Minimum Switch Off Time vs. Temperature

Figure 20. NCP1402SN50T1 Minimum Switch Off Time vs. Temperature

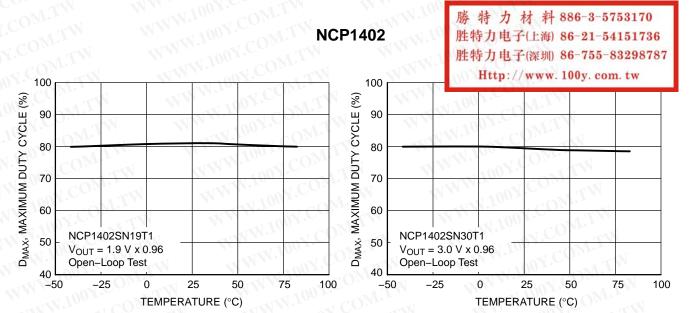


Figure 21. NCP1402SN19T1 Maximum Duty Cycle vs. Temperature

Figure 22. NCP1402SN30T1 Maximum Duty Cycle vs. Temperature

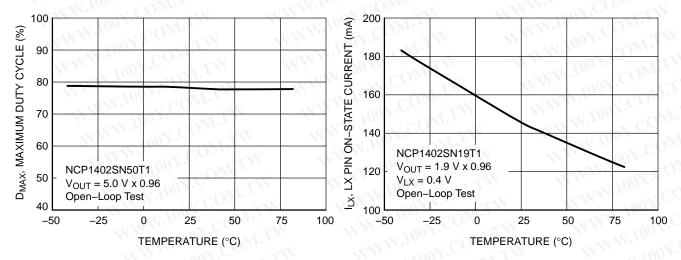


Figure 23. NCP1402SN50T1 Maximum Duty Cycle vs. Temperature

Figure 24. NCP1402SN19T1 LX Pin On-State Current vs. Temperature

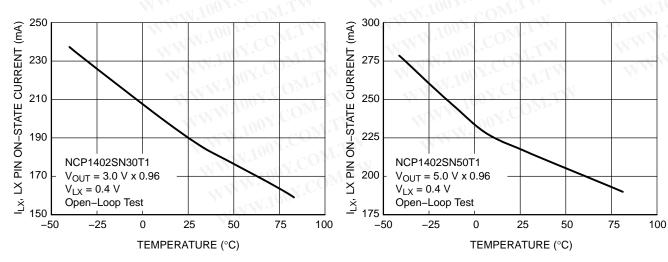


Figure 25. NCP1402SN30T1 LX Pin On-State Current vs. Temperature

Figure 26. NCP1402SN50T1 LX Pin On-State Current vs. Temperature

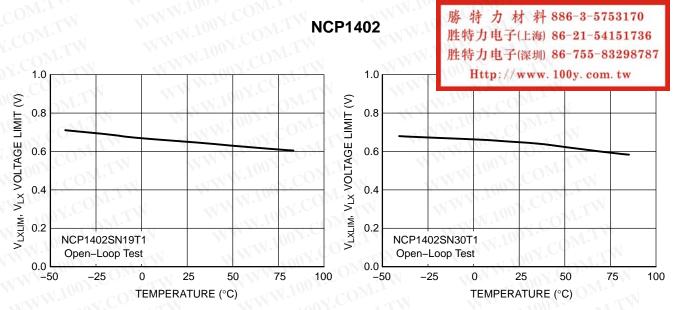


Figure 27. NCP1402SN19T1 V<sub>LX</sub> Voltage Limit vs. Temperature

Figure 28. NCP1402SN30T1 V<sub>LX</sub> Voltage Limit vs. Temperature

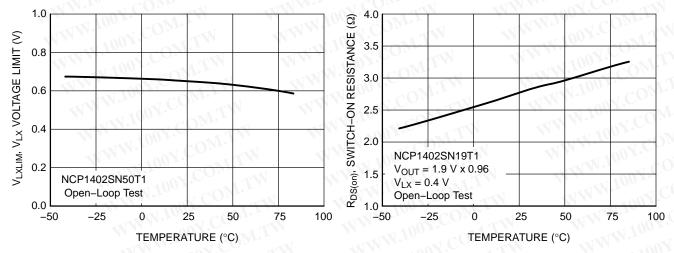


Figure 29. NCP1402SN50T1 V<sub>LX</sub> Voltage Limit vs. Temperature

Figure 30. NCP1402SN19T1 Switch-on Resistance vs. Temperature

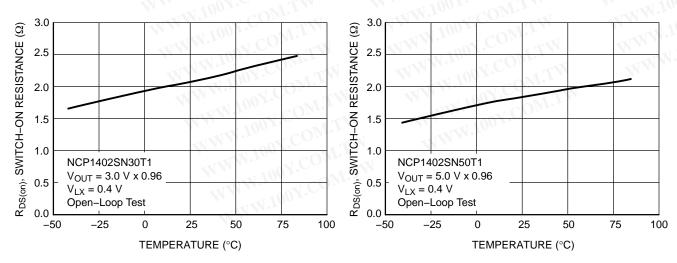


Figure 31. NCP1402SN30T1 Switch-on Resistance vs. Temperature

Figure 32. NCP1402SN50T1 Switch-on Resistance vs. Temperature



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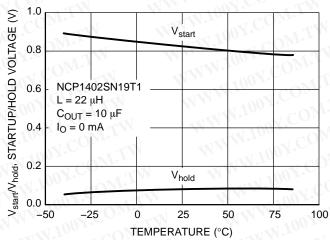


Figure 33. NCP1402SN19T1 Startup/Hold Voltage vs. Temperature

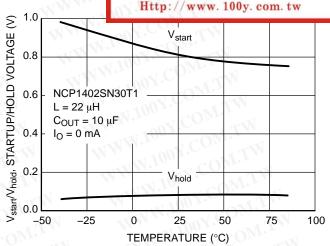


Figure 34. NCP1402SN30T1 Startup/Hold Voltage vs. Temperature

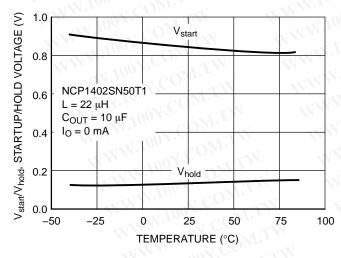


Figure 35. NCP1402SN50T1 Startup/Hold Voltage vs. Temperature

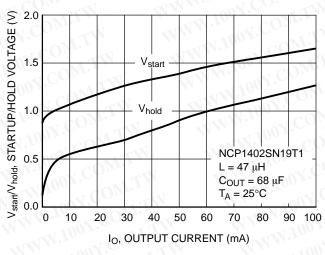


Figure 36. NCP1402SN19T1 Startup/Hold Voltage vs. Output Current

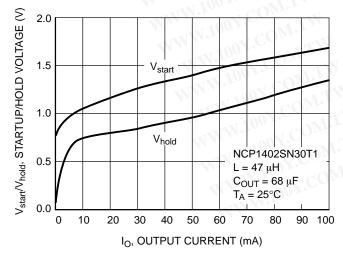


Figure 37. NCP1402SN30T1 Startup/Hold Voltage vs. Output Current

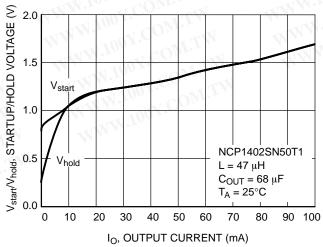
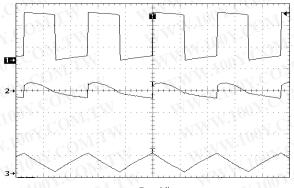


Figure 38. NCP1402SN50T1 Startup/Hold Voltage vs. Output Current

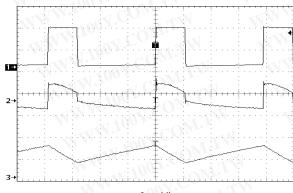


5 μs/div

 $V_{OUT}$  = 1.9 V,  $V_{in}$  = 1.2 V,  $I_{O}$  = 30 mA, L = 47  $\mu H,\ C_{OUT}$  = 68  $\mu F$ 

- 1. V<sub>LX</sub>, 1.0 V/div
- 2. V<sub>OUT</sub>, 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

Figure 39. NCP1402SN19T1 Operating Waveforms (Medium Load)

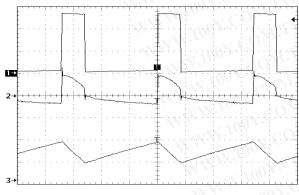


2 μs/div

 $V_{OUT}$  = 3.0 V,  $V_{in}$  = 1.2 V,  $I_{O}$  = 30 mA, L = 47  $\mu H,\ C_{OUT}$  = 68  $\mu F$ 

- 1. V<sub>LX</sub>, 2.0 V/div
- 2. V<sub>OUT</sub>, 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

Figure 41. NCP1402SN30T1 Operating Waveforms (Medium Load)

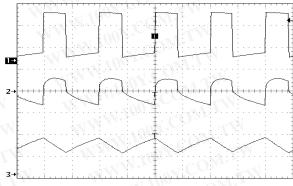


2 μs/div

 $V_{OUT} = 5.0$  V,  $V_{in} =$  1.5 V,  $I_{O} = 30$  mA,  $L = 47~\mu H,~C_{OUT} = 68~\mu F$ 

- 1. V<sub>LX</sub>, 2.0 V/div
- 2. V<sub>OUT</sub>, 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

Figure 43. NCP1402SN50T1 Operating Waveforms (Medium Load)

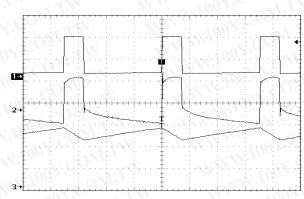


5 μs/div

 $V_{OUT}$  = 1.9 V,  $V_{in}$  = 1.2 V,  $I_{O}$  = 70 mA, L = 47  $\mu H,~C_{OUT}$  = 68  $\mu F$ 

- 1. V<sub>LX</sub>, 1.0 V/div
- 2. V<sub>OUT</sub>, 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

## Figure 40. NCP1402SN19T1 Operating Waveforms (Heavy Load)

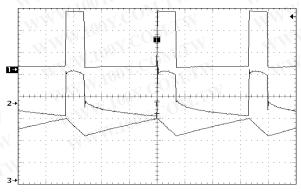


2 μs/div

 $V_{OUT}$  = 3.0 V,  $V_{in}$  = 1.2 V,  $I_{O}$  = 70 mA, L = 47  $\mu$ H,  $C_{OUT}$  = 68  $\mu$ F

- 1. V<sub>LX</sub>, 2.0 V/div
- 2. V<sub>OUT</sub>, 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

Figure 42. NCP1402SN30T1 Operating Waveforms (Heavy Load)

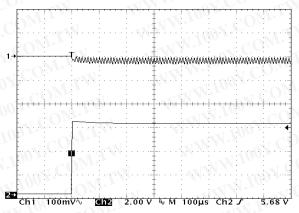


2 us/div

 $V_{OUT}$  = 5.0 V,  $V_{in}$  = 1.5 V,  $I_{O}$  = 60 mA, L = 47  $\mu H,~C_{OUT}$  = 68  $\mu F$ 

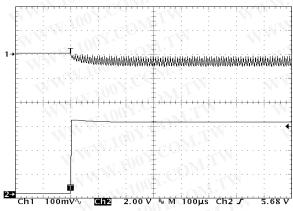
- 1. V<sub>LX</sub>, 2.0 V/div
- 2.  $V_{OUT}$ , 20 mV/div, AC coupled
- 3. I<sub>L</sub>, 100 mA/div

# Figure 44. NCP1402SN50T1 Operating Waveforms (Heavy Load)



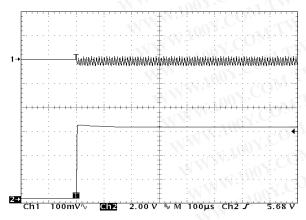
- $V_{in}$  = 1.2 V, L = 47  $\mu H,\ C_{OUT}$  = 68  $\mu F$
- 1.  $V_{OUT} = 1.9 V (AC coupled), 100 mV/div$
- 2.  $I_0 = 0.1 \text{ mA to } 80 \text{ mA}$

Figure 45. NCP1402SN19T1 Load Transient Response



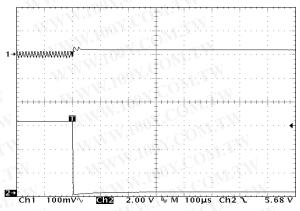
- $V_{in}$  = 1.5 V, L = 47  $\mu$ H,  $C_{OUT}$  = 68  $\mu$ F
- 1.  $V_{OUT} = 3.0 \text{ V (AC coupled)}$ , 100 mV/div
- 2.  $I_0 = 0.1 \text{ mA to } 80 \text{ mA}$

Figure 47. NCP1402SN30T1 Load Transient Response



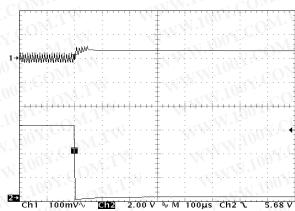
- $V_{in}$  = 2.4 V, L = 47  $\mu$ H,  $C_{OUT}$  = 68  $\mu$ F
- 1.  $V_{OUT} = 5.0 \text{ V (AC coupled)}, 100 \text{ mV/div}$
- 2.  $I_0 = 0.1 \text{ mA to } 80 \text{ mA}$

Figure 49. NCP1402SN50T1 Load Transient Response



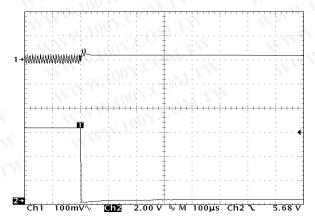
- $V_{in}$  = 1.2 V, L = 47  $\mu$ H,  $C_{OUT}$  = 68  $\mu$ F
- 1.  $V_{OUT} = 1.9 V (AC coupled), 100 mV/div$
- 2.  $I_0 = 80 \text{ mA to } 0.1 \text{ mA}$

Figure 46. NCP1402SN19T1 Load Transient Response



- $V_{in}$  = 1.5 V, L = 47  $\mu H,\ C_{OUT}$  = 68  $\mu F$
- 1.  $V_{OUT} = 3.0 \text{ V (AC coupled)}, 100 \text{ mV/div}$
- 2.  $I_0 = 80 \text{ mA to } 0.1 \text{ mA}$

Figure 48. NCP1402SN30T1 Load Transient Response



- $V_{in}$  = 2.4 V, L = 47  $\mu H,\ C_{OUT}$  = 68  $\mu F$
- 1.  $V_{OUT} = 5.0 \text{ V (AC coupled)}, 100 \text{ mV/div}$
- 2.  $I_0 = 80 \text{ mA to } 0.1 \text{ mA}$

Figure 50. NCP1402SN50T1 Load Transient Response

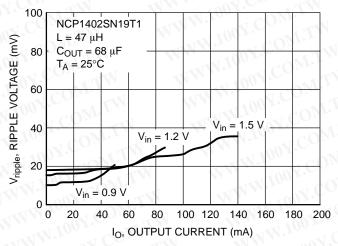


Figure 51. NCP1402SN19T1 Ripple Voltage vs.
Output Current

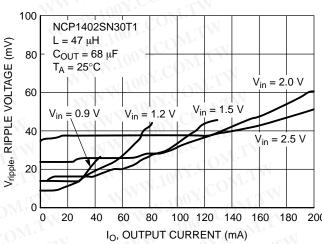


Figure 52. NCP1402SN30T1 Ripple Voltage vs.
Output Current

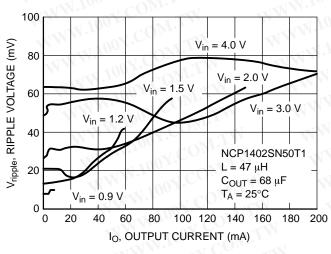


Figure 53. NCP1402SN50T1 Ripple Voltage vs.
Output Current

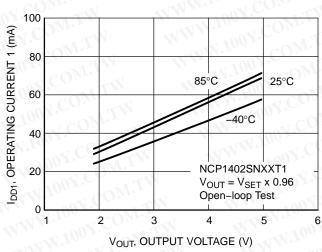


Figure 54. NCP1402SNXXT1 Operating Current 1 vs. Output Voltage

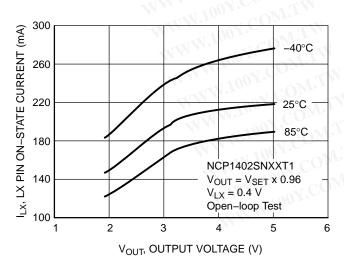


Figure 55. NCP1402SNXXT1 Pin On-state Current vs. Output Voltage

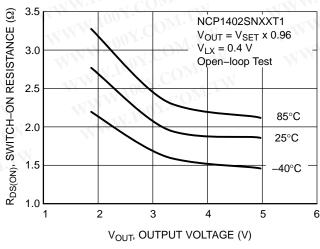


Figure 56. NCP1402SNXXT1 Switch-On Resistance vs. Output Voltage

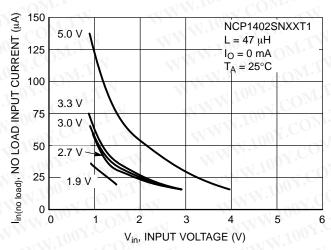


Figure 57. NCP1402SNXXT1 No Load Input Current vs. Input Voltage

## DETAILED OPERATING DESCRIPTION

#### Operation

The NCP1402 series are monolithic power switching regulators optimized for applications where power drain must be minimized. These devices operate as variable frequency, voltage mode boost regulators and designed to operate in continuous conduction mode. Potential applications include low powered consumer products and battery powered portable products.

The NCP1402 series are low noise variable frequency voltage–mode DC–DC converters, and consist of Soft–Start circuit, feedback resistor, reference voltage, oscillator, PFM comparator, PFM control circuit, current limit circuit and power switch. Due to the on–chip feedback resistor network, the system designer can get the regulated output voltage from 1.8 V to 5 V with a small number of external components. The operating current is typically 30  $\mu A$  (V $_{OUT}=1.9$  V), and can be further reduced to about 0.6  $\mu A$  when the chip is disabled (V $_{CE}<0.3$  V).

The NCP1402 operation can be best understood by examining the block diagram in Figure 2. PFM comparator monitors the output voltage via the feedback resistor. When the feedback voltage is higher than the reference voltage, the power switch is turned off. As the feedback voltage is lower than reference voltage and the power switch has been off for at least a period of minimum off-time decided by PFM oscillator, the power switch is then cycled on for a period of on-time also decided by PFM oscillator, or until current limit signal is asserted. When the power switch is on, current ramps up in the inductor, storing energy in the magnetic field. When the power switch is off, the energy in the magnetic field is transferred to output filter capacitor and the load. The output filter capacitor stores the charge while the inductor current is high, then holds up the output voltage until next switching cycle.

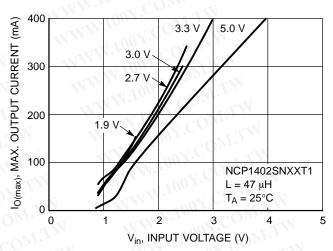


Figure 58. NCP1402SNXXT1 Maximum Output
Current vs. Input Voltage

#### Soft-Start

There is a Soft–Start circuit in NCP1402. When power is applied to the device, the Soft–Start circuit pumps up the output voltage to approximately 1.5 V at a fixed duty cycle, the level at which the converter can operate normally. What is more, the startup capability with heavy loads is also improved.

#### Regulated Converter Voltage (V<sub>OUT</sub>)

The  $V_{OUT}$  is set by an internal feedback resistor network. This is trimmed to a selected voltage from 1.8 to 5.0 V range in 100 mV steps with an accuracy of  $\pm 2.5\%$ .

#### **Current Limit**

The NCP1402 series utilizes cycle-by-cycle current limiting as a means of protecting the output switch MOSFET from overstress and preventing the small value inductor from saturation. Current limiting is implemented by monitoring the output MOSFET current build-up during conduction, and upon sensing an overcurrent conduction immediately turning off the switch for the duration of the oscillator cycle.

The voltage across the output MOSFET is monitored and compared against a reference by the VLX limiter. When the threshold is reached, a signal is sent to the PFM controller block to terminate the power switch conduction. The current limit threshold is typically set at 350 mA.

#### **Enable / Disable Operation**

The NCP1402 series offer IC shut—down mode by chip enable pin (CE pin) to reduce current consumption. An internal pullup resistor tied the CE pin to OUT pin by default i.e. user can float the pin CE for permanent "On". When voltage at pin CE is equal or greater than 0.9 V, the chip will be enabled, which means the regulator is in normal operation. When voltage at pin CE is less than 0.3 V, the chip is disabled, which means IC is shutdown.

Important: DO NOT apply a voltage between 0.3 V and 0.9 V to pin CE as this is the CE pin's hyteresis voltage range. Clearly defined output states can only be obtained by applying voltage out of this range.

#### **APPLICATIONS CIRCUIT INFORMATION**

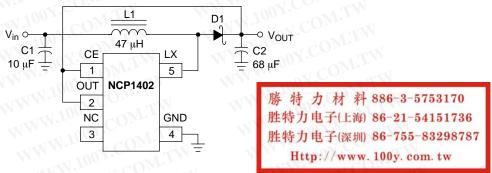


Figure 59. Typical Application Circuit

#### Step-up Converter Design Equations

NCP1402 step—up DC—DC converter designed to operate in continuous conduction mode can be defined by:

Calculation	Equation
VEWW.	$\leq M \left( \frac{V_{in}^2}{V_{OUT} I_{Omax}} \right)$
I <sub>PK</sub>	$\frac{(V_{in} - V_{s})t_{on}}{L} + I_{min}$
I <sub>min</sub>	$\frac{(t_{ON} + t_{Off})I_{O}}{t_{Off}} - \frac{(V_{IN} - V_{S})t_{ON}}{2L}$
t <sub>off</sub>	$\frac{(V_{in} - V_{s})t_{on}}{(V_{OUT} + V_{F} - V_{in})}$
ΔQ	(IL - IO)toff
V <sub>ripple</sub>	$\approx \frac{\Delta Q}{C_{OUT}} + (I_L - I_O)ESR$

#### \*NOTES:

 $\begin{array}{lll} I_{PK} & - & \text{Peak inductor current} \\ I_{min} & - & \text{Minimum inductor current} \\ I_{O} & - & \text{Desired dc output current} \end{array}$ 

 $I_{Omax}$  - Desired maximum dc output current

I<sub>L</sub> - Average inductor current

Vin - Nominal operating dc input voltage

V<sub>OUT</sub> – Desired dc output voltage V<sub>F</sub> – Diode forward voltage

V<sub>S</sub> – Saturation voltage of the internal FET switch ΔQ – Charge stores in the C<sub>OUT</sub> during charging up

V<sub>ripple</sub> - Output ripple voltage

ESR - Equivalent series resistance of the output capacitor

M – An empirical factor, when  $V_{OUT} \ge 3.0 \text{ V}$ ,  $M = 8 \times 10^{-6}$ , otherwise  $M = 5.3 \times 10^{-6}$ .

#### **EXTERNAL COMPONENT SELECTION**

#### Inductor

The NCP1402 is designed to work well with a 47  $\mu H$  inductor in most applications. 47  $\mu H$  is a sufficiently low value to allow the use of a small surface mount coil, but large

enough to maintain low ripple. Low inductance values supply higher output current, but also increase the ripple and reduce efficiency. Note that values below 27  $\mu H$  is not recommended due to NCP1402 switch limitations. Higher inductor values reduce ripple and improve efficiency, but also limit output current.

The inductor should have small DCR, usually less than 1  $\Omega$  to minimize loss. It is necessary to choose an inductor with saturation current greater than the peak current which the inductor will encounter in the application.

#### Diode

The diode is the main source of loss in DC–DC converters. The most importance parameters which affect their efficiency are the forward voltage drop,  $V_{\rm F}$ , and the reverse recovery time,  $t_{\rm rr}$ . The forward voltage drop creates a loss just by having a voltage across the device while a current flowing through it. The reverse recovery time generates a loss when the diode is reverse biased, and the current appears to actually flow backwards through the diode due to the minority carriers being swept from the P–N junction. A Schottky diode with the following characteristics is recommended:

Small forward voltage,  $V_F < 0.3 \text{ V}$ 

Small reverse leakage current

Fast reverse recovery time/ switching speed

Rated current larger than peak inductor current

 $I_{rated} > I_{PK}$ 

Reverse voltage larger than output voltage,

 $V_{reverse} > V_{OUT}$ 

#### **Input Capacitor**

The input capacitor can stabilize the input voltage and minimize peak current ripple from the source. The value of the capacitor depends on the impedance of the input source used. Small Equivalent Series Resistance (ESR) Tantalum or ceramic capacitor with value of  $10~\mu F$  should be suitable.

#### **Output Capacitor**

The output capacitor is used for sustaining the output voltage when the internal MOSFET is switched on and smoothing the ripple voltage. Low ESR capacitor should be used to reduce output ripple voltage. In general, a 47 uF to 68 uF low ESR (0.15  $\Omega$  to 0.30  $\Omega$ ) Tantalum capacitor should be appropriate. For applications where space is a critical factor, two parallel 22 uF low profile SMD ceramic capacitors can be used.

An evaluation board of NCP1402 has been made in the size of 23 mm x 20 mm only, as shown in Figures 60 and 61. Please contact your ON Semiconductor representative for availability. The evaluation board schematic diagram, the artwork and the silkscreen of the surface mount PCB are shown below:

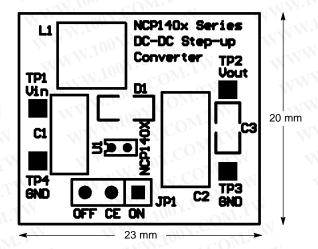


Figure 60. NCP1402 PFM Step-Up DC-DC Converter Evaluation Board Silkscreen

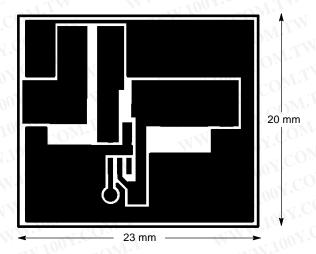


Figure 61. NCP1402 PFM Step-Up DC-DC Converter Evaluation Board Artwork (Component Side)

#### **Components Supplier**

Parts	Supplier	Part Number	Description	Phone
Inductor, L1	Sumida Electric Co. Ltd.	CD54-470L	Inductor 47 μH / 0.72 A	(852)-2880-6688
Schottky Diode, D1	ON Semiconductor Corp.	MBR0520LT1	Schottky Power Rectifier	(852)–2689–0088
Output Capacitor, C2	KEMET Electronics Corp.	T494D686K010AS	Low ESR Tantalum Capacitor 68 µF / 10 V	(852)–2305–1168
Input Capacitor, C1	KEMET Electronics Corp.	T491C106K016AS	Low Profile Tantalum Capacitor 10 μF / 16 V	(852)–2305–1168

#### **PCB Layout Hints**

#### Grounding

One point grounding should be used for the output power return ground, the input power return ground, and the device switch ground to reduce noise as shown in Figure 62, e.g.: C2 GND, C1 GND, and U1 GND are connected at one point in the evaluation board. The input ground and output ground traces must be thick enough for current to flow through and for reducing ground bounce.

#### **Power Signal Traces**

Low resistance conducting paths should be used for the power carrying traces to reduce power loss so as to improve efficiency (short and thick traces for connecting the inductor L can also reduce stray inductance), e.g.: short and thick traces listed below are used in the evaluation board:

- 1. Trace from TP1 to L1
- 2. Trace from L1 to Lx pin of U1
- 3. Trace from L1 to anode pin of D1
- 4. Trace from cathode pin of D1 to TP2

#### **Output Capacitor**

The output capacitor should be placed close to the output terminals to obtain better smoothing effect on the output ripple.

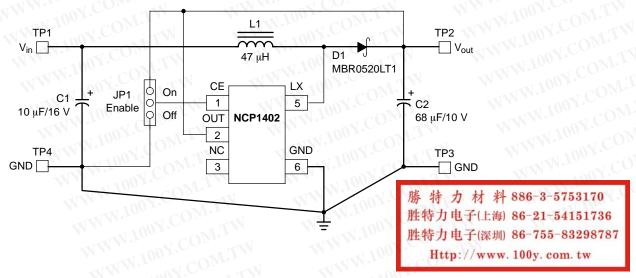
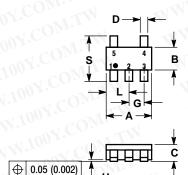
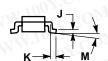


Figure 62. NCP1402 Evaluation Board Schematic Diagram

#### PACKAGE DIMENSIONS

SOT23-5 (TSOP-5, SC59-5) SN SUFFIX CASE 483-02 ISSUE C 勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw





#### NOTES

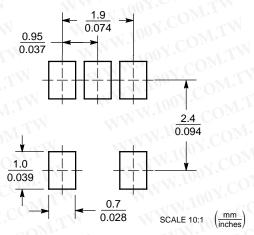
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.

  3. MAXIMUM LEAD THICKNESS INCLUDES
- MAXIMUM LEAD THICKNESS INCLUDES
   LEAD FINISH THICKNESS. MINIMUM LEAD
   THICKNESS IS THE MINIMUM THICKNESS
   OF BASE MATERIAL.

  4. A AND B DIMENSIONS DO NOT INCLUDE
- A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.1142	0.1220	
В	1.30	1.70	0.0512	0.0669	
С	0.90	1.10	0.0354	0.0433	
D	0.25	0.50	0.0098	0.0197	
G	0.85	1.05	0.0335	0.0413	
Н	0.013	0.100	0.0005	0.0040	
J	0.10	0.26	0.0040	0.0102	
K	0.20	0.60	0.0079	0.0236	
L	1.25	1.55	0.0493	0.0610	
M	0	10	0	10	
s	2.50	3.00	0.0985	0.1181	

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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